

isc Silicon NPN Power Transistor

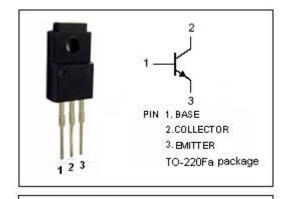
2SC3709A

DESCRIPTION

- · Low Collector Saturation Voltage-
 - : V_{CE(sat)}= 0.4V(Max)@I_C= 6A
- · Good Linearity of hFE
- Complement to Type 2SA1451A

APPLICATIONS

• Designed for high current switching applications



ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
Vсво	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	6	V
lc	Collector Current-Continuous	12	А
I _{CP} *	Pulse Collector Current	30	А
lв	Base Current-Continuous	2	А
Pc	Collector Power Dissipation @ T _C =25℃	30	W
TJ	Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature Range	-55~150	°C

11.	3-	→ s	•	/F
PA C	-L		- [6
•	0			
*			1 7	J-J-L
k				v
.	ļ	_	 ← _J	
		→ R →C		→ N → D
		m	20.0	
	DIM	MIN	MAX	
	Α	16.85	17.15	
2.1	В	9.54		1
	$\overline{}$		10.10	
	С	4.35	4.65	
	C D	4.35 0.75	4.65 0.90	ć
	C D F	4.35 0.75 3.20	4.65 0.90 3.40	
6 6 8	C D F G	4.35 0.75	4.65 0.90 3.40 7.20	
	C D F	4.35 0.75 3.20 6.90	4.65 0.90 3.40	
	C D F G	4.35 0.75 3.20 6.90 5.15	4.65 0.90 3.40 7.20 5.45 0.75 13.65	
	C D F G H J K	4.35 0.75 3.20 6.90 5.15 0.45	4.65 0.90 3.40 7.20 5.45 0.75 13.65 1.30	
	C D F G H J	4.35 0.75 3.20 6.90 5.15 0.45 13.35 1.10 4.98	4.65 0.90 3.40 7.20 5.45 0.75 13.65 1.30 5.18	
	C D F G H J K L N	4.35 0.75 3.20 6.90 5.15 0.45 13.35 1.10 4.98 4.85	4.65 0.90 3.40 7.20 5.45 0.75 13.65 1.30 5.18	
	C D F G H J K L N Q	4.35 0.75 3.20 6.90 5.15 0.45 13.35 1.10 4.98 4.85 2.55	4.65 0.90 3.40 7.20 5.45 0.75 13.65 1.30 5.18 5.15 3.25	
	C D F G H J K L N	4.35 0.75 3.20 6.90 5.15 0.45 13.35 1.10 4.98 4.85 2.55	4.65 0.90 3.40 7.20 5.45 0.75 13.65 1.30 5.18 5.15 3.25 2.90	
	C D F G H J K L N Q	4.35 0.75 3.20 6.90 5.15 0.45 13.35 1.10 4.98 4.85 2.55	4.65 0.90 3.40 7.20 5.45 0.75 13.65 1.30 5.18 5.15 3.25	

^{*}Tested in QT-2 transistor graphic instrument and test condition is IB=2A,VCE=5V.

0.2

 μ S



ISC Silicon NPN Power Transistor

2SC3709A

ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 50mA ; I _B = 0	50			V	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 0.3A			0.4	V	
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 0.3A			1.2	V	
Ісво	Collector Cutoff Current	V _{CB} = 60V; I _E = 0			10	μА	
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			10	μА	
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 1V	70		240		
h _{FE-2}	DC Current Gain	I _C = 6A; V _{CE} = 1V	40				
Сов	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1MHz		180		pF	
f _T	Current-Gain—Bandwidth Product	I _C = 1A; V _{CE} = 5V		90		MHz	
Switching Times							
ton	Turn-on Time			0.2		μS	
t _{stg}	Storage Time	I_{B1} = $-I_{B2}$ = 0.3A, R_L = 5 Ω ; V_{CC} \approx 30V,		1.0		μS	

♦ h_{FE-1} Classifications

Fall Time

0	Y
70-140	120-240

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications. ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

isc website: www.iscsemi.com

isc & iscsemi is registered trademark